



# 安徽富信半导体科技有限公司

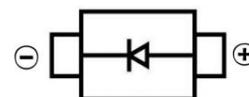
ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

DSR1A-DSR1M

## SOD-123FL General Purpose Rectifier Diode 通用整流二极管

### ■ Features 特点

Low forward voltage drop 低正向压降  
 Low reverse leakage current 低反向漏电流  
 High surge current capability 高浪涌电流能力  
 Surface mount device 表面贴装器件  
 Case 封装:SOD-123FL



### ■ Maximum Rating 最大额定值

( $T_A=25^{\circ}\text{C}$  unless otherwise noted 如无特殊说明, 温度为  $25^{\circ}\text{C}$ )

Characteristic 特性参数	Symbol 符号	DSR 1A	DSR 1B	DSR 1D	DSR 1G	DSR 1J	DSR 1K	DSR 1M	Unit 单位
Marking 印字		S1A	S1B	S1D	S1G	S1J	S1K	S1M	
Peak Reverse Voltage 反向峰值电压	$V_{RRM}$	50	100	200	400	600	800	1000	V
DC Reverse Voltage 直流反向电压	$V_R$	50	100	200	400	600	800	1000	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	35	70	140	280	420	560	700	V
Forward Rectified Current 正向整流电流	$I_F$	1							A
Peak Surge Current 峰值浪涌电流	$I_{FSM}$	30							A
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	80							$^{\circ}\text{C}/\text{W}$
Junction and Storage Temperature 结温和储藏温度	$T_J, T_{stg}$	150 $^{\circ}\text{C}$ , -55to+150 $^{\circ}\text{C}$							

### ■ Electrical Characteristics 电特性

( $T_A=25^{\circ}\text{C}$  unless otherwise noted 如无特殊说明, 温度为  $25^{\circ}\text{C}$ )

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位	Test Condition 测试条件
Forward Voltage 正向电压	$V_F$		1.0	1.1	V	$I_F=1\text{A}$
Reverse Current( $T_A=25^{\circ}\text{C}/$ ) 反向电流( $T_A=100^{\circ}\text{C}/$ )	$I_R$			5 50	$\mu\text{A}$	$V_R=V_{RRM}$
Diode Capacitance 二极管电容	$C_D$		15		pF	$V_R=4\text{V}, f=1\text{MHz}$



## ■ Typical Characteristic Curve 典型特性曲线

FIG.1-TYPICAL FORWARD CHARACTERISTICS

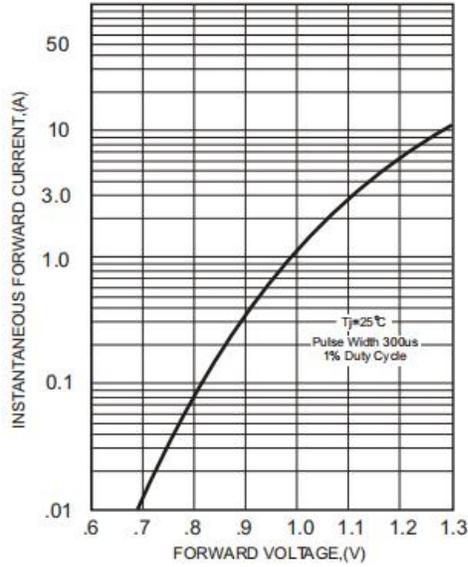


FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE

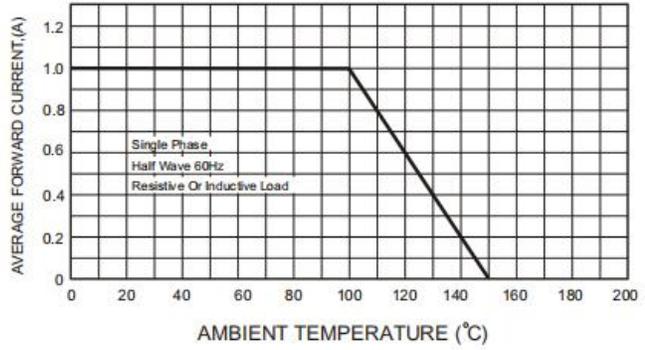


FIG.4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

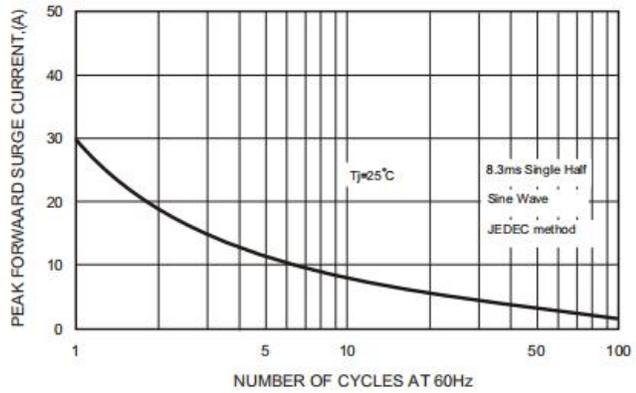


FIG.3 - TYPICAL REVERSE CHARACTERISTICS

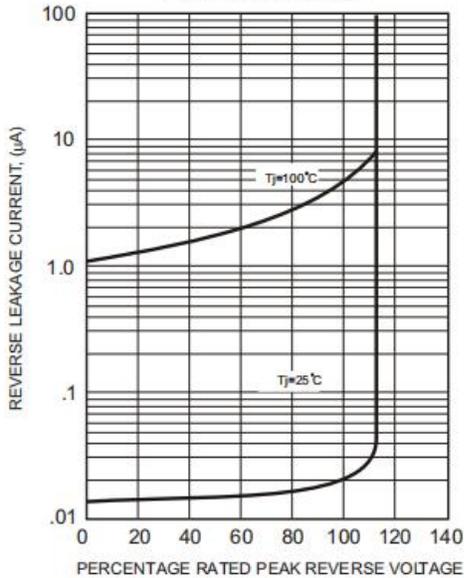
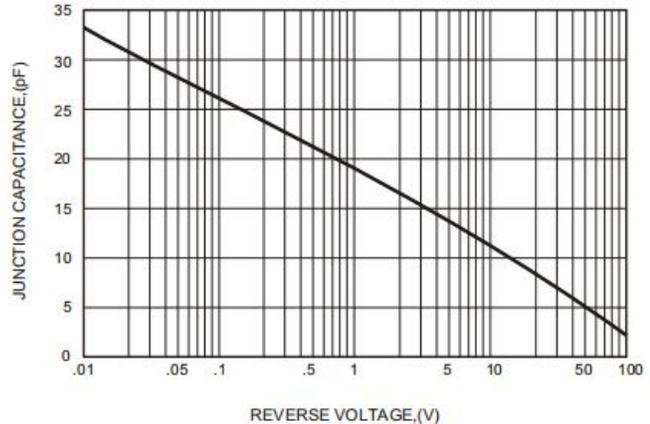
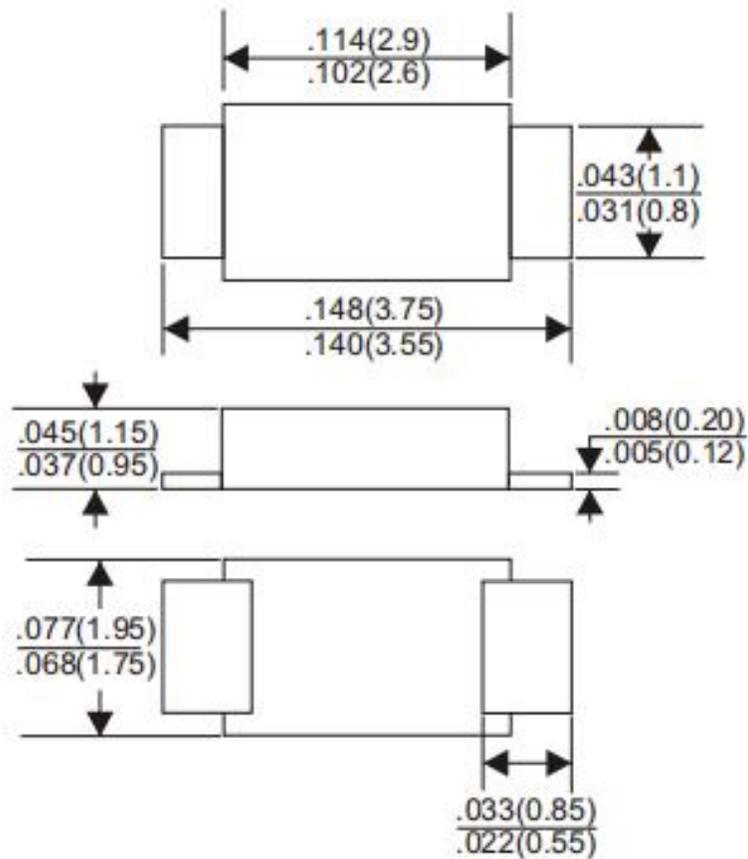


FIG.5-TYPICAL JUNCTION CAPACITANCE



## ■Dimension 外形封装尺寸



Dimensions in inches and (millimeters)